

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device having a portion thereof formed from a wafer of semiconductive material by a laser etching process comprising:
~~a substrate of semiconductive wafer material having a surface;~~
~~a semiconductor device having a plurality of bond pads located in the center of a surface thereof~~
~~portion thereof attached to a portion of the substrate; and~~
~~an interposer comprising silicon oxide coated silicon having the same size as the semiconductor~~
~~device and a centrally located aperture therein having a portion of a surface thereof~~
~~connected to the semiconductor device having the plurality of bond pads of the~~
~~semiconductor device located in the aperture of the interposer to allow the connection of~~
~~bond wires to the bond pads of the semiconductor device and to circuits of another~~
~~surface of the interposer substrate, the interposer having a laser roughened surface using a~~
~~first laser at a first location increasing the surface area of a surface of the interposer to~~
~~adhere mold material thereto in a molding operation, the surface roughened prior to the~~
~~semiconductor device being attached to the interposer, the aperture in the interposer filled~~
~~with mold material after the connection of bond wires between the bond pads of the~~
~~semiconductor device and the circuits of the interposer;~~
~~and~~
~~a portion of resist, contamination, and oxidation located on a portion of the surface of the~~
~~substrate of semiconductive wafer material removed by laser etching of the resist,~~
~~contamination, and oxidation from the surface of the substrate of semiconductive wafer~~
~~material using a second laser forming a portion of an automolding system, the portion of~~
~~resist, contamination, and oxidation removed by the second laser forming a portion of the~~
~~automolding system prior to the encapsulation of a portion of the semiconductor device~~
~~in the automolding system.~~
2. (Canceled)

3. (Previously Presented) The semiconductor device according to claim 1, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

4. (Currently Amended) The semiconductor device according to claim 1, wherein the interposer substrate comprises a ball-grid-array interposer substrate.

5. (Previously Presented) The semiconductor device according to claim 1, further comprising a vision system for detecting the resist.

6. (Previously Presented) The semiconductor device according to claim 5, wherein the vision system comprises:

a laser scanning system for detecting changes in a pattern of the substrate.

Claims 7 - 11 (Canceled)

12. (Withdrawn) A semiconductor device having a portion formed by a laser etching process on a substrate of semiconductive material having a surface comprising: resist located on at least a portion of the surface having a portion thereof removed by etching the resist from the at least a portion of the surface of the substrate using a laser forming a roughened surface on the surface of the substrate of semiconductive material increasing the surface area of the surface to adhere mold material thereto .

13. (Withdrawn) The semiconductor device according to claim 12, wherein the laser comprises a laser associated with an automolding system.

14. (Withdrawn) The semiconductor device according to claim 12, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

15. (Withdrawn) The semiconductor device according to claim 12, wherein the substrate comprises a ball-grid-array substrate.

16. (Withdrawn) The semiconductor device according to claim 12, further comprising a vision system for detecting the resist.

17. (Withdrawn) The semiconductor device according to claim 16, wherein the vision system comprises: a laser scanning system for detecting changes in a pattern of the substrate.

Claims 18 – 23 (Canceled)